

BTA12-600BW3G, BTA12-800BW3G

Triacs Silicon Bidirectional Thyristors

Designed for high performance full-wave ac control applications where high noise immunity and high commutating di/dt are required.

Features

- Blocking Voltage to 800 V
- On-State Current Rating of 12 A RMS at 25°C
- Uniform Gate Trigger Currents in Three Quadrants
- High Immunity to dV/dt – 2000 V/μs minimum at 125°C
- Minimizes Snubber Networks for Protection
- Industry Standard TO-220AB Package
- High Commutating dI/dt – 2.5 A/ms minimum at 125°C
- Internally Isolated (2500 V_{RMS})
- These are Pb-Free Devices

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

| Rating | Symbol | Value | Unit |
|---|--|--|--------------------|
| Peak Repetitive Off-State Voltage (Note 1) (T _J = -40 to 125°C, Sine Wave, 50 to 60 Hz, Gate Open) BTA12-600BW3G BTA12-800BW3G | V _{DRM} , V _{RRM} | 600 800 | V |
| On-State RMS Current (Full Cycle Sine Wave, 60 Hz, T _C = 80°C) | I _{T(RMS)} | 12 | A |
| Peak Non-Repetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T _C = 25°C) | I _{TSM} | 105 | A |
| Circuit Fusing Consideration (t = 8.3 ms) | I ² t | 46 | A ² sec |
| Non-Repetitive Surge Peak Off-State Voltage (T _J = 25°C, t = 10ms) | V _{DSM} / V _{RSM} | V _{DSM} /V _{RSM} +100 | V |
| Peak Gate Current (T _J = 125°C, t = 20ms) | I _{GM} | 4.0 | A |
| Peak Gate Power (Pulse Width ≤ 1.0 μs, T _C = 80°C) | P _{GM} | 20 | W |
| Average Gate Power (T _J = 125°C) | P _{G(AV)} | 1.0 | W |
| Operating Junction Temperature Range | T _J | -40 to +125 | °C |
| Storage Temperature Range | T _{stg} | -40 to +150 | °C |
| RMS Isolation Voltage (t = 300 ms, R.H. ≤ 30%, T _A = 25°C) | V _{iso} | 2500 | V |

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

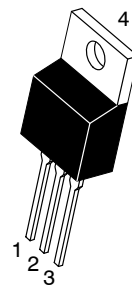
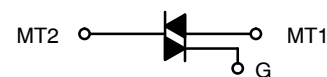
1. V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.



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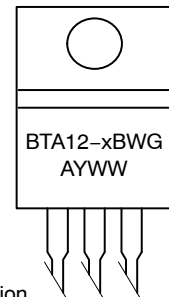
TRIACS 12 AMPERES RMS 600 thru 800 VOLTS



TO-220AB
CASE 221A
STYLE 12

x = 6 or 8
A = Assembly Location
Y = Year
WW = Work Week
G = Pb-Free Package

MARKING DIAGRAM



PIN ASSIGNMENT

| | |
|---|-----------------|
| 1 | Main Terminal 1 |
| 2 | Main Terminal 2 |
| 3 | Gate |
| 4 | No Connection |

ORDERING INFORMATION

| Device | Package | Shipping |
|---------------|-----------------------|-----------------|
| BTA12-600BW3G | TO-220AB (Pb-Free) | 50 Units / Rail |
| BTA12-800BW3G | TO-220AB (Pb-Free) | 50 Units / Rail |

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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THERMAL CHARACTERISTICS

| Characteristic | Symbol | Value | Unit |
|---|-----------------|-------|------|
| Thermal Resistance, Junction-to-Case (AC) | $R_{\theta JC}$ | 2.5 | °C/W |
| Junction-to-Ambient | $R_{\theta JA}$ | 60 | |
| Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 seconds | T_L | 260 | °C |

ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise noted; Electricals apply in both directions)

| Characteristic | Symbol | Min | Typ | Max | Unit |
|----------------|--------|-----|-----|-----|------|
|----------------|--------|-----|-----|-----|------|

OFF CHARACTERISTICS

| | | | | | |
|--|--------------------|---------------------------|---|--------------|----|
| Peak Repetitive Blocking Current ($V_D = \text{Rated } V_{DRM}, V_{RRM}; \text{Gate Open}$) | I_{DRM}, I_{RRM} | – | – | 0.005 2.0 | mA |
| | | $T_J = 25^\circ\text{C}$ | | | |
| | | $T_J = 125^\circ\text{C}$ | | | |

ON CHARACTERISTICS

| | | | | | |
|---|----------|-----|---|------|----|
| Peak On-State Voltage (Note 2) ($I_{TM} = \pm 17 \text{ A Peak}$) | V_{TM} | – | – | 1.55 | V |
| Gate Trigger Current (Continuous dc) ($V_D = 12 \text{ V}, R_L = 30 \Omega$) | I_{GT} | 2.5 | – | 50 | mA |
| MT2(+), G(+) | | 2.5 | – | 50 | |
| MT2(+), G(–) | | 2.5 | – | 50 | |
| MT2(–), G(–) | | 2.5 | – | 50 | |
| Holding Current ($V_D = 12 \text{ V}, \text{Gate Open}, \text{Initiating Current} = \pm 100 \text{ mA}$) | I_H | – | – | 50 | mA |
| Latching Current ($V_D = 12 \text{ V}, I_G = 60 \text{ mA}$) | I_L | – | – | 70 | mA |
| MT2(+), G(+) | | – | – | 80 | |
| MT2(+), G(–) | | – | – | 70 | |
| MT2(–), G(–) | | – | – | 70 | |
| Gate Trigger Voltage ($V_D = 12 \text{ V}, R_L = 30 \Omega$) | V_{GT} | 0.5 | – | 1.7 | V |
| MT2(+), G(+) | | 0.5 | – | 1.1 | |
| MT2(+), G(–) | | 0.5 | – | 1.1 | |
| MT2(–), G(–) | | 0.5 | – | 1.1 | |
| Gate Non-Trigger Voltage ($T_J = 125^\circ\text{C}$) | V_{GD} | 0.2 | – | – | V |
| MT2(+), G(+) | | 0.2 | – | – | |
| MT2(+), G(–) | | 0.2 | – | – | |
| MT2(–), G(–) | | 0.2 | – | – | |

DYNAMIC CHARACTERISTICS

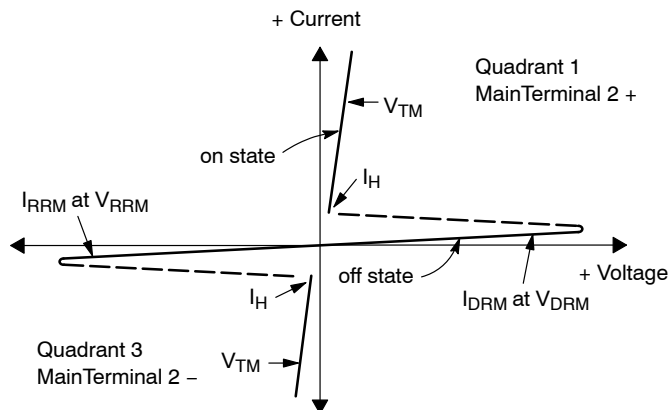
| | | | | | |
|---|-------------|------|---|----|------------------|
| Rate of Change of Commutating Current, See Figure 10. (Gate Open, $T_J = 125^\circ\text{C}$, No Snubber) | $(di/dt)_c$ | 2.5 | – | – | A/ms |
| Critical Rate of Rise of On-State Current ($T_J = 125^\circ\text{C}, f = 120 \text{ Hz}, I_G = 2 \times I_{GT}, tr \leq 100 \text{ ns}$) | di/dt | – | – | 50 | A/ μs |
| Critical Rate of Rise of Off-State Voltage ($V_D = 0.66 \times V_{DRM}$, Exponential Waveform, Gate Open, $T_J = 125^\circ\text{C}$) | dV/dt | 2000 | – | – | V/ μs |

2. Indicates Pulse Test: Pulse Width $\leq 2.0 \text{ ms}$, Duty Cycle $\leq 2\%$.

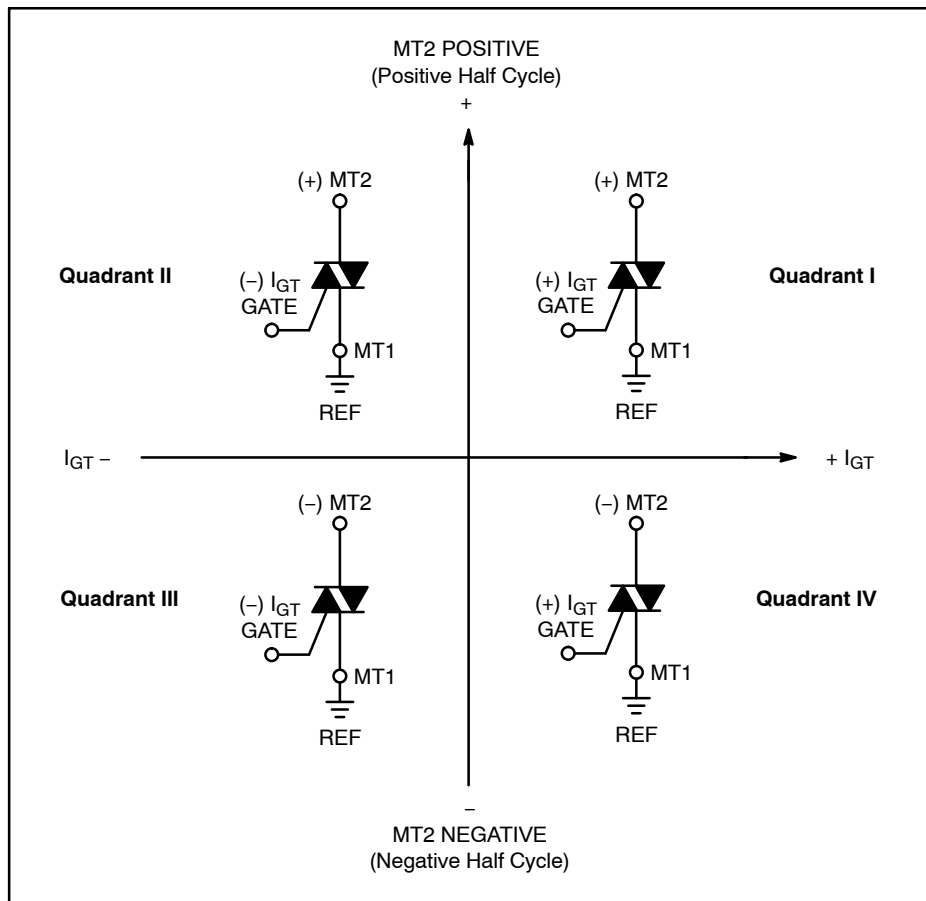
BTA12-600BW3G, BTA12-800BW3G

Voltage Current Characteristic of Triacs (Bidirectional Device)

| Symbol | Parameter |
|-----------|---|
| V_{DRM} | Peak Repetitive Forward Off State Voltage |
| I_{DRM} | Peak Forward Blocking Current |
| V_{RRM} | Peak Repetitive Reverse Off State Voltage |
| I_{RRM} | Peak Reverse Blocking Current |
| V_{TM} | Maximum On State Voltage |
| I_H | Holding Current |



Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

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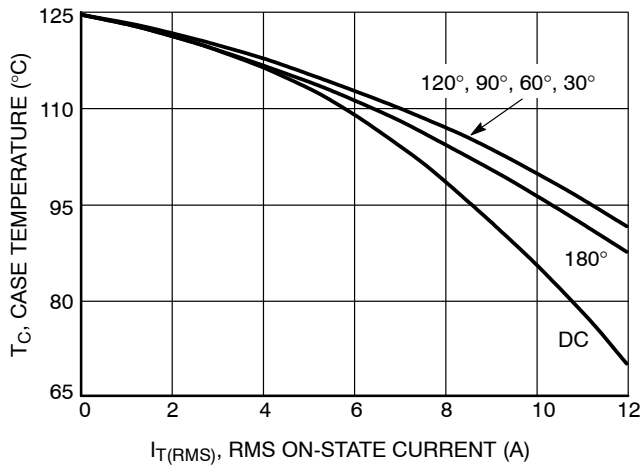


Figure 1. RMS Current Derating

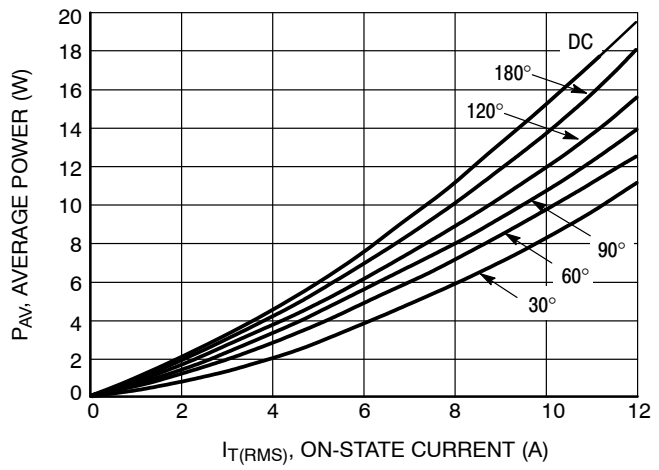


Figure 2. On-State Power Dissipation

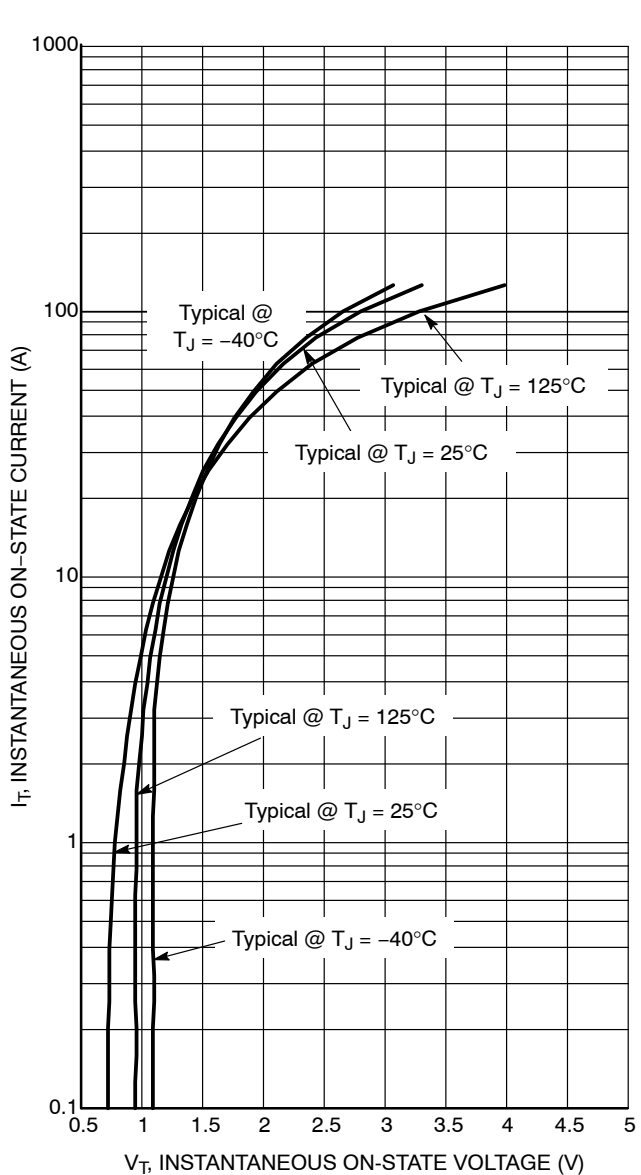


Figure 3. On-State Characteristics

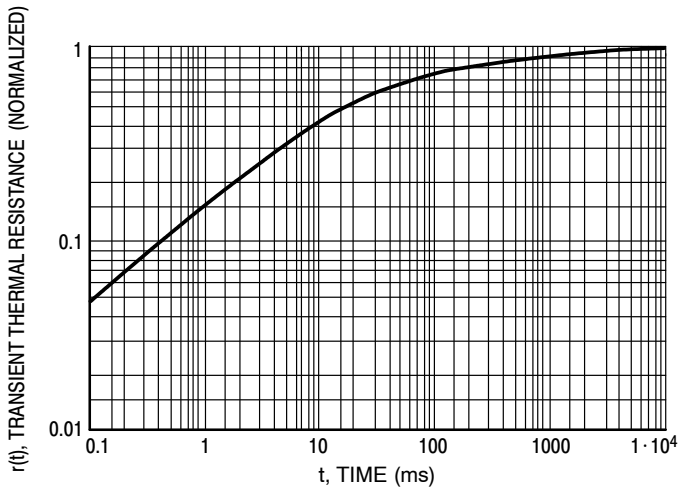


Figure 4. Thermal Response

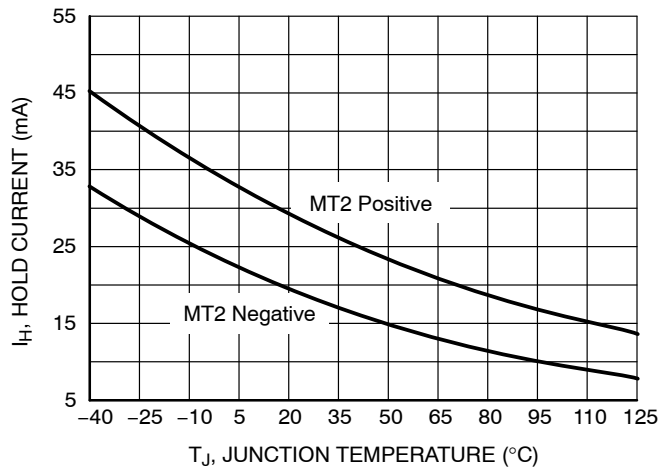


Figure 5. Hold Current Variation

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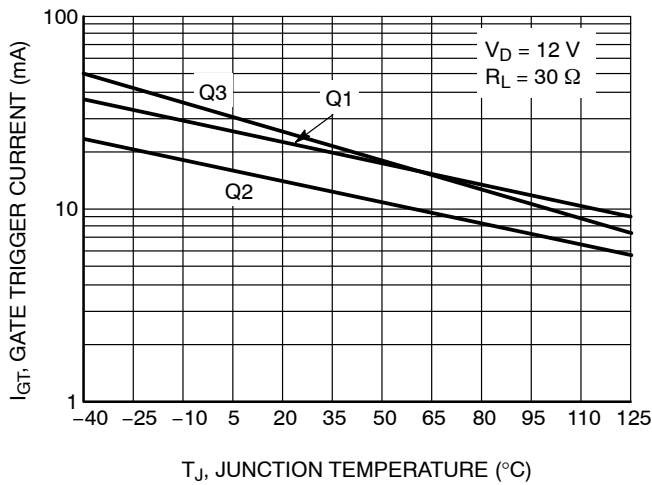


Figure 6. Gate Trigger Current Variation

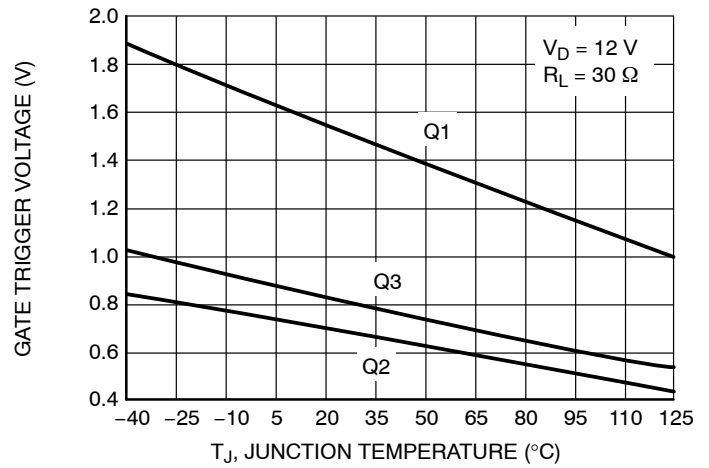


Figure 7. Gate Trigger Voltage Variation

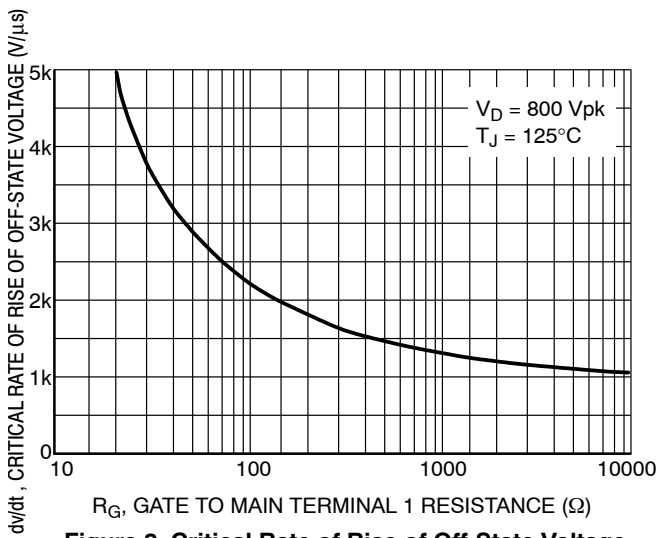


Figure 8. Critical Rate of Rise of Off-State Voltage (Exponential Waveform)

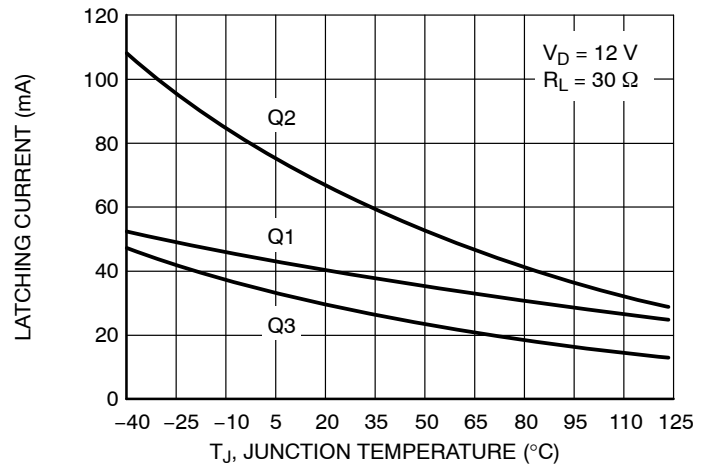
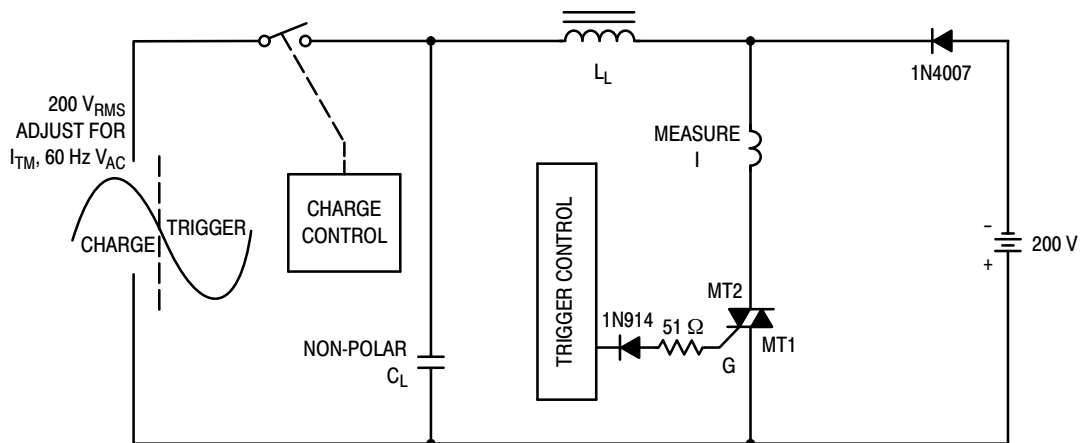


Figure 10. Latching Current Variation



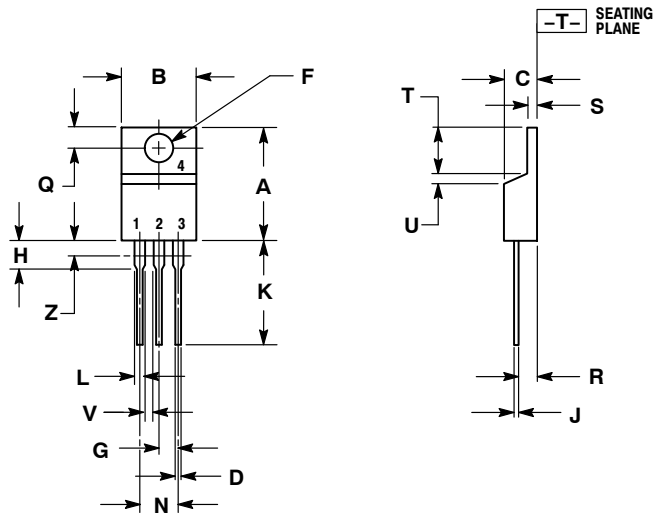
Note: Component values are for verification of rated $(di/dt)_c$. See AN1048 for additional information.

Figure 9. Simplified Test Circuit to Measure the Critical Rate of Rise of Commutating Current $(di/dt)_c$

BTA12-600BW3G, BTA12-800BW3G

PACKAGE DIMENSIONS

TO-220
CASE 221A-07
ISSUE O




NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.570 | 0.620 | 14.48 | 15.75 |
| B | 0.380 | 0.405 | 9.66 | 10.28 |
| C | 0.160 | 0.190 | 4.07 | 4.82 |
| D | 0.025 | 0.035 | 0.64 | 0.88 |
| F | 0.142 | 0.147 | 3.61 | 3.73 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| H | 0.110 | 0.155 | 2.80 | 3.93 |
| J | 0.014 | 0.022 | 0.36 | 0.55 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.39 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| V | 0.045 | --- | 1.15 | --- |
| Z | --- | 0.080 | --- | 2.04 |

STYLE 12:

- PIN 1. MAIN TERMINAL 1
2. MAIN TERMINAL 2
3. GATE
4. NOT CONNECTED

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